



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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BYI-1/1F/1T/1Z

BYISTORS FOR LINEAR
POWER AMPLIFIERS

GENERAL DESCRIPTION The BYI-1/1F/1T/1Z is a semiconductor device specifically designed for use in linear amplifier bias circuitry. The byistor acts as a low impedance D.C. bias source which has two modes for thermal compensation.	CASE OUTLINE
ABSOLUTE MAXIMUM RATINGS Maximum Power Dissipation @ 25°C 11 Watts Maximum Voltage and Current BVces Collector to Emitter Voltage 55 Volts BVebo Emitter to Base Voltage 4.0 Volts Ic Collector Current 0.7 A Maximum Temperatures Storage Temperature - 65 to +150°C Operating Junction Temperature +150°C	

ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout	Power Output	F = 400 MHz	3			Watts
Pin	Power Input	Vcc = 28 Volts			0.2	Watts
Pg	Power Gain		11.8	13		dB
η_c	Efficiency			60		%
VSWR	Load Mismatch Tolerance				30:1	

BVebo	Emitter to Base Breakdown	Ie = 5 mA	4.0			Volts
BVces	Collector to Emitter	Ic = 20 mA	55			Volts
BVceo	Breakdown	Ie = 50 mA	30			Volts
BVcbo	Collector to Emitter	Ic = __ mA				Volts
Icbo	Breakdown	Vc = __ Volts				mA
Cob	Collector to Base Breakdown	Vcb = 28 V, F = 1		4.5		pF
hFE	Collector to Base Current	MHz	10	45	150	
θ_{jc}	Output Capacitance	Vce = 5 V, Ic = 100 A			16	°C/W
	DC - Current Gain					
	Thermal Resistance					

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